

FH8707

N-Channel Enhancement Mode Power MOSFET

Description

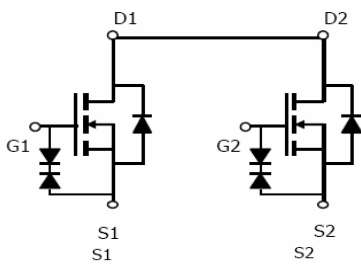
The FH8707 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

Application

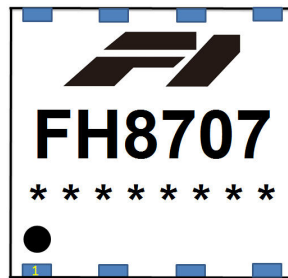
- PWM application
- Load switch

General Features

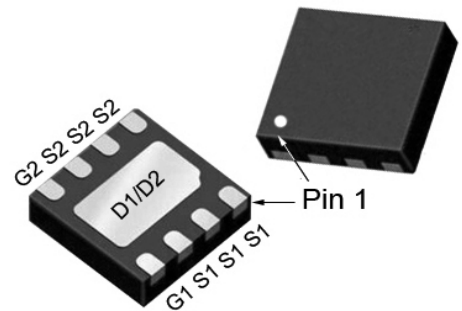
- $V_{DS} = 16V, I_D = 13A$
 - $R_{DS(ON)} < 7\text{ m}\Omega @ V_{GS} = 4.5V$
 - $R_{DS(ON)} < 8\text{ m}\Omega @ V_{GS} = 3.8V$
 - $R_{DS(ON)} < 9\text{ m}\Omega @ V_{GS} = 2.5V$
- ESD Rating: 2000V HBM
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package



Schematic diagram



Marking and pin assignment



DFN3x3-8L Pin assignment and Top / Bottom View

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|------------|------|
| Drain-Source Voltage | V_{DS} | 16 | V |
| Gate-Source Voltage | V_{GS} | ± 10 | V |
| Drain Current-Continuous | I_D | 13 | A |
| Drain Current-Pulsed (Note 1) | I_{DM} | 53 | A |
| Maximum Power Dissipation (TA=25°C) | P_D | 3 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | °C |

Thermal Characteristic

| | | | |
|--|-----------------|------|------|
| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 41.7 | °C/W |
|--|-----------------|------|------|

Electrical Characteristics (TA=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---------------------------------|------------|-------------------------------|-----|-----|-----|---------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = 250\mu A$ | 16 | | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 13V, V_{GS} = 0V$ | - | - | 1 | μA |

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|--------------|--|------|------|----------|------------|
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 10V, V_{DS}=0V$ | - | - | ± 10 | μA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 0.45 | 0.8 | 1.2 | V |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=4.5V, I_D=6.0A$ | | 4.5 | 7 | m Ω |
| | | $V_{GS}=3.8V, I_D=5.0A$ | | 5.5 | 8 | m Ω |
| | | $V_{GS}=2.5V, I_D=4.0A$ | | 7 | 9 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS}=5V, I_D=5A$ | - | 20 | - | S |
| Dynamic Characteristics (Note4) | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$ | - | 1310 | - | PF |
| Output Capacitance | C_{oss} | | - | 264 | - | PF |
| Reverse Transfer Capacitance | C_{rss} | | - | 235 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=10V, R_L=1.35\Omega$ $V_{GS}=5V, R_{GEN}=3\Omega$ | - | 6 | | nS |
| Turn-on Rise Time | t_r | | - | 13 | | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 52 | | nS |
| Turn-Off Fall Time | t_f | | - | 16 | | nS |
| Total Gate Charge | Q_g | $V_{DS}=10V, I_D=7A,$ $V_{GS}=4.5V$ | - | 15 | | nC |
| Gate-Source Charge | Q_{gs} | | - | 3 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 7 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V_{SD} | $V_{GS}=0V, I_S=1A$ | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | I_S | | - | - | 7 | A |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

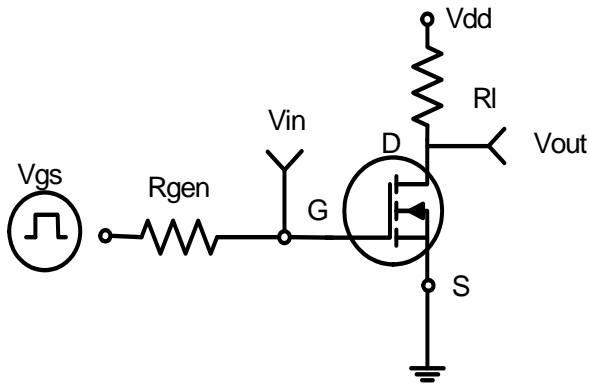


Figure 1: Switching Test Circuit

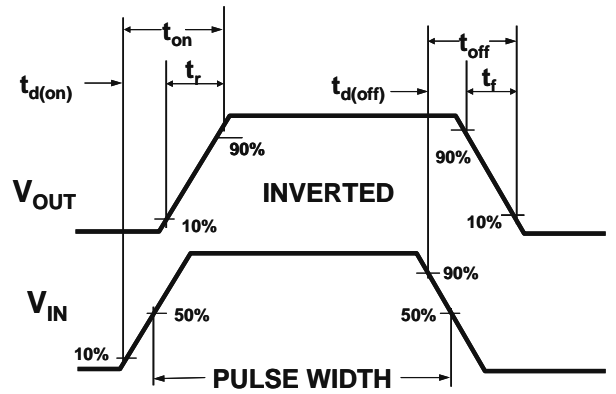


Figure 2: Switching Waveforms

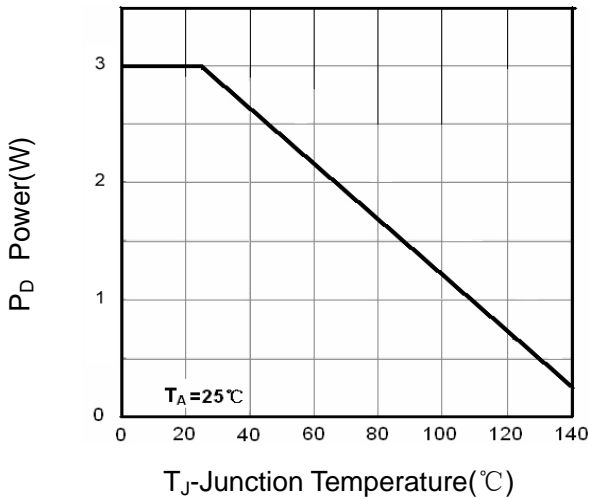


Figure 3 Power Dissipation

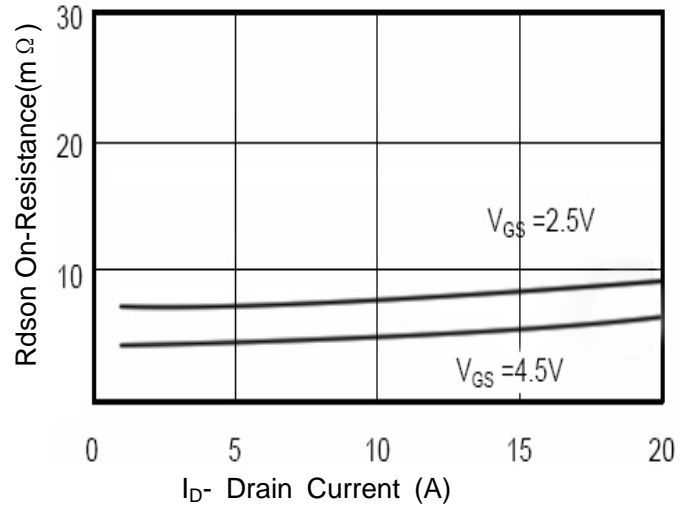


Figure 4 Drain-Source On-Resistance

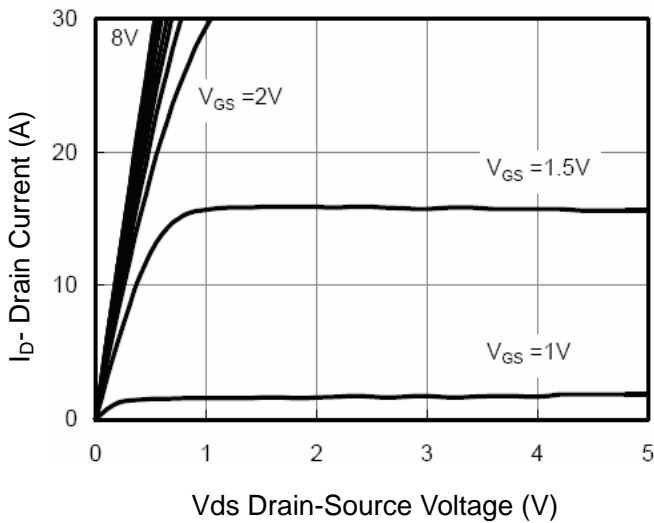


Figure 5 Output CHARACTERISTICS

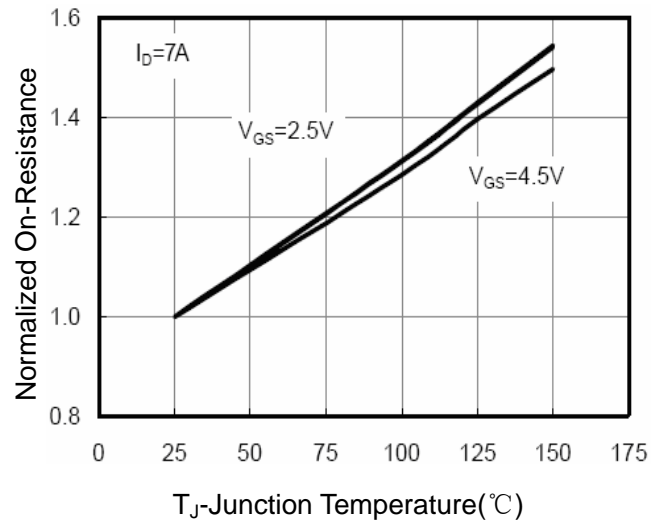
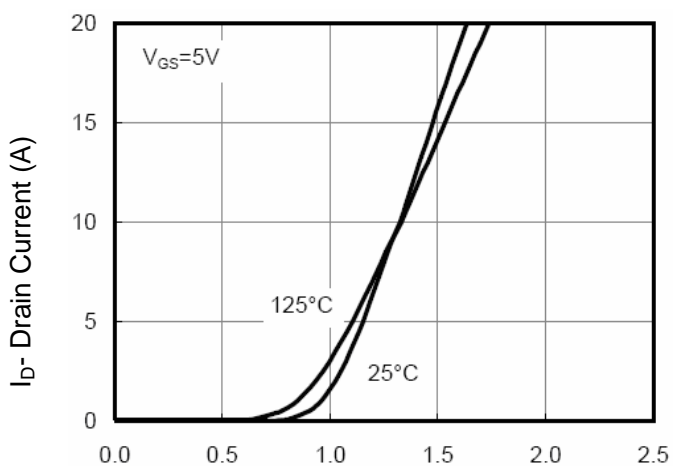
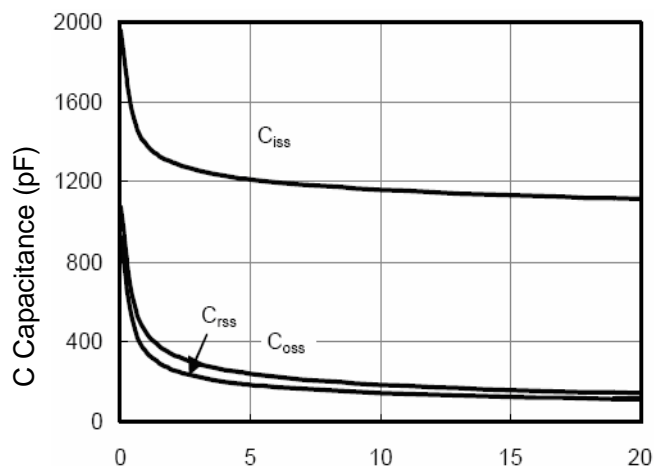


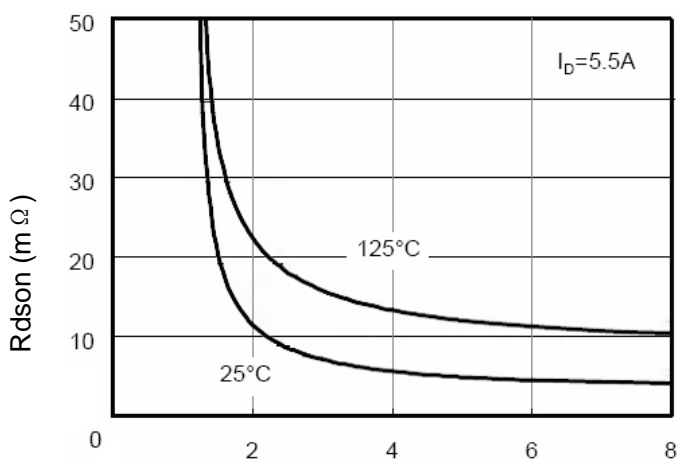
Figure 6 Drain-Source On-Resistance



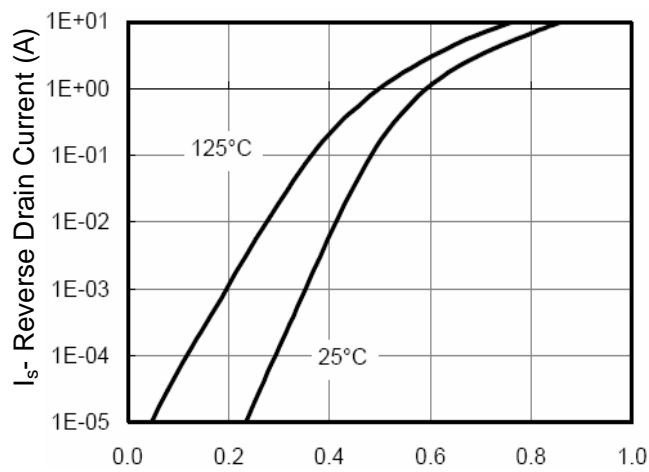
Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



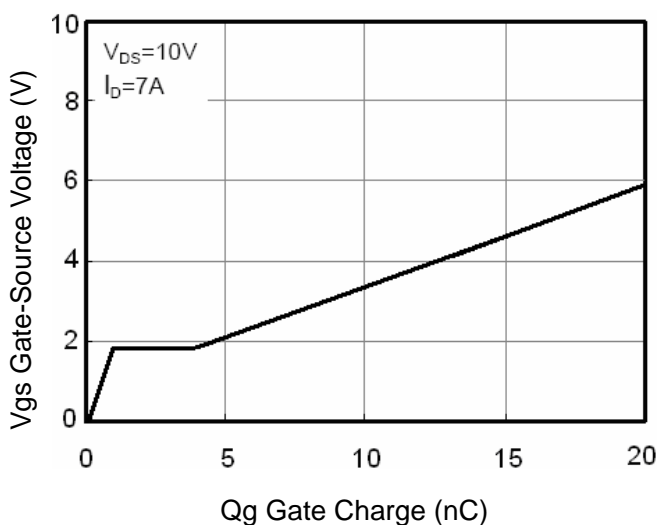
Vds Drain-Source Voltage (V)
Figure 8 Capacitance vs Vds



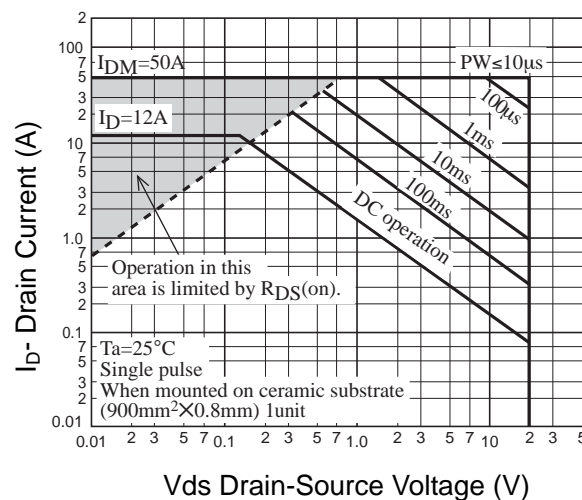
Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Qg Gate Charge (nC)
Figure 11 Gate Charge



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area

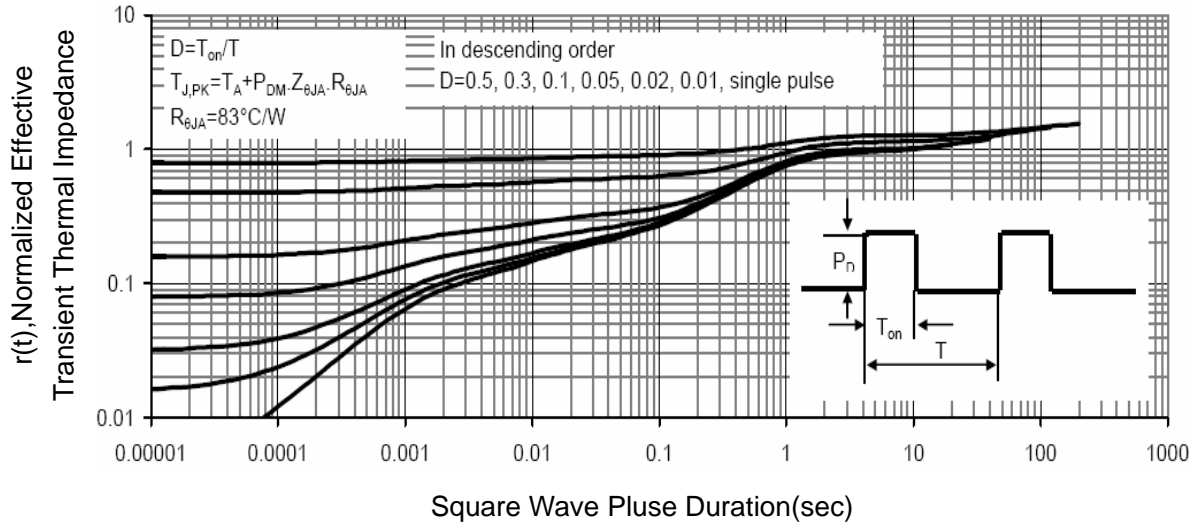
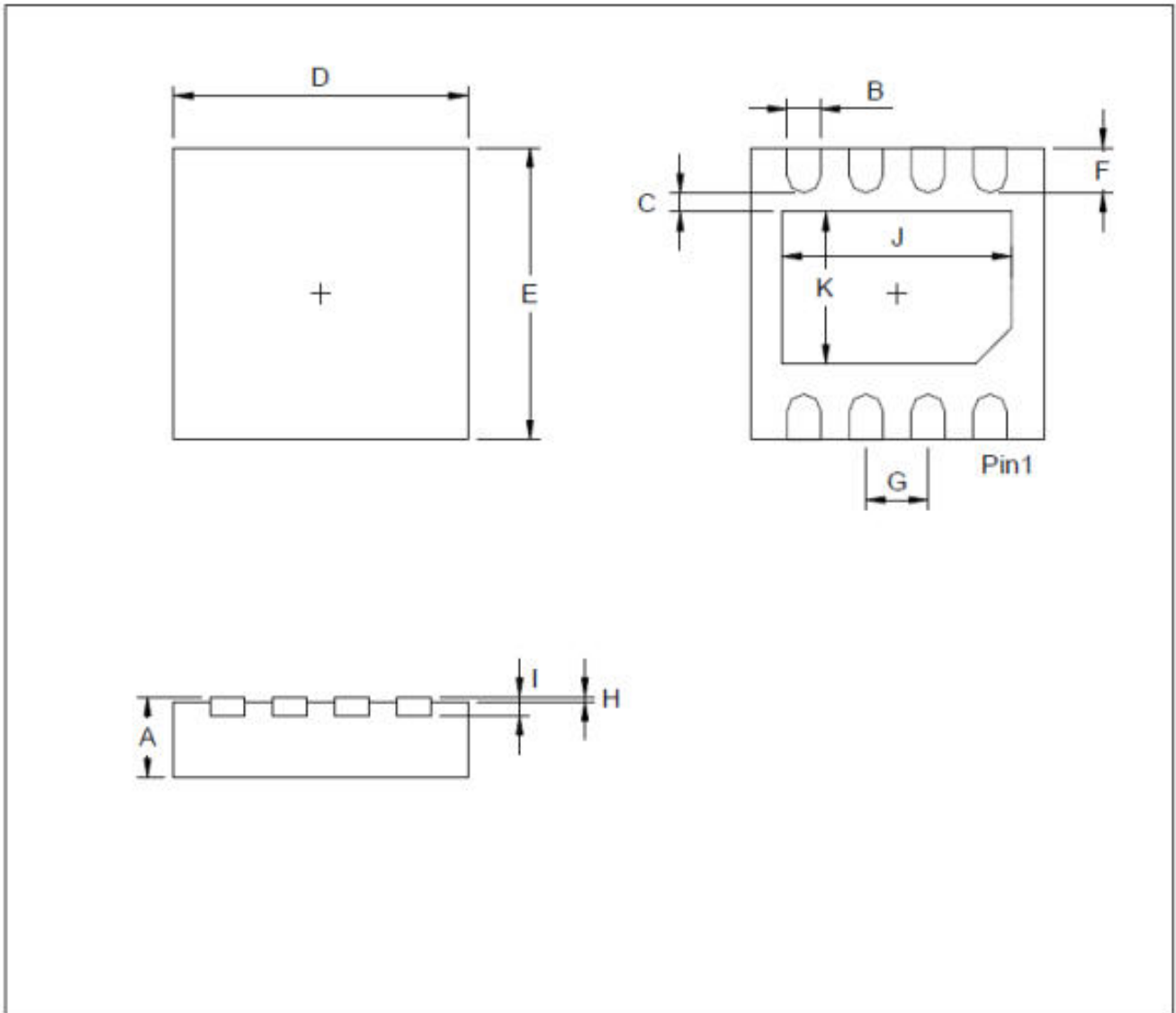


Figure 13 Normalized Maximum Transient Thermal Impedance

Package Outline Dimensions : DFN3*3-8L



| Dimension | mm | | | Dimension | mm | | |
|-----------|-------|------|-------|-----------|------|-------|------|
| | Min. | Typ. | Max. | | Min. | Typ. | Max. |
| A | 0.7 | | 0.8 | I | | 0.203 | |
| B | 0.25 | | 0.35 | J | 2.2 | | 2.4 |
| C | 0.2 | | | K | 1.4 | | 1.6 |
| D | 2.924 | | 3.076 | | | | |
| E | 2.924 | | 3.076 | | | | |
| F | 0.324 | | 0.476 | | | | |
| G | | 0.65 | | | | | |
| H | 0 | | 0.05 | | | | |

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